



## Features

- Very Low Noise 1.1 dB Typ.
- High +36 dBm Typ. IP3
- 16 dB Typical Gain
- 6.0 Volt Bias
- 26% High Power Added Efficiency

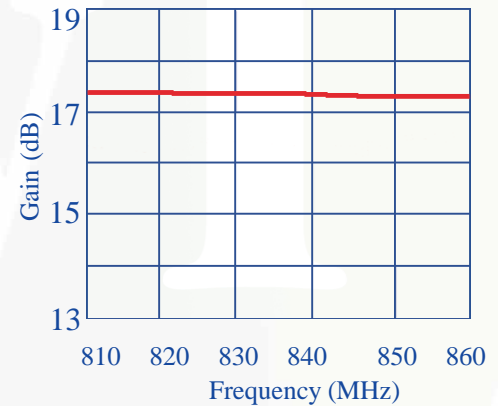
The MPS-0808A9-85 is a low noise, high dynamic range amplifier designed for ultralinear receiver applications in the 806 to 849 MHz frequency range. The circuit is matched to 50 ohm and employs a single stage GaAs FET with internal matching to provide exceptional noise figure, 1.1 dB combined with extremely high IP3, +36 dBm. Typical applications are base station receivers, Tower mounted LNA's, smart antenna systems and receiver multi-couplers.

## Specifications

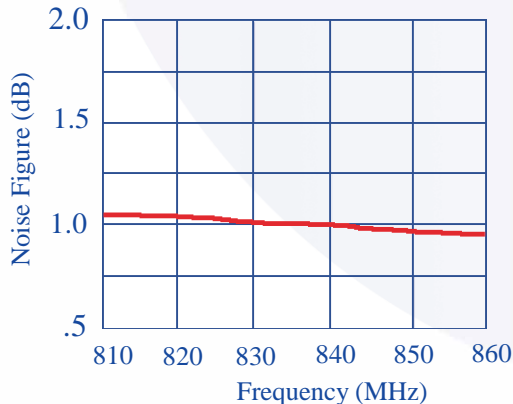
- Electrical at 25°C, V<sub>dd</sub>= 6.0 V, Z<sub>o</sub>= 50 Ω

Symbol	Parameter	Min.	Typical	Max	Unit
Freq	Frequency Range	806		849	MHz
SSG	Small Signal Gain	14	16		dB
P1dB	P out at 1 dB Compression		+21.5		dBm
IP3	Third-order Intercept	+33	+36.0		dBm
NF	Noise Figure		1.1	1.5	dB
VSWR	Input VSWR		2.0:1	2.5:1	
ΔGOF	Gain Variation over Freq.		+/-0.2	+/-0.5	dB
ΔGOT	Gain Variation over Temp.		-0.15		dB/°C
I <sub>dd</sub>	DC Current		180	250	mA
PAE	Power Added Efficiency		26		%

Gain vs. Frequency



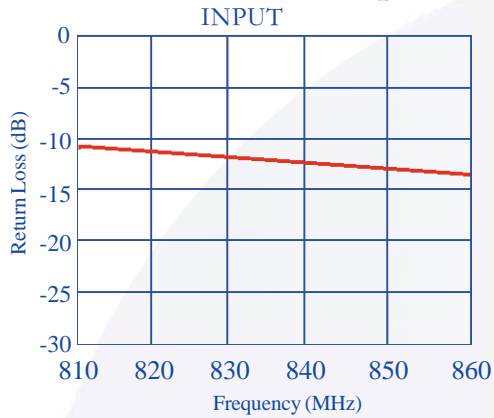
Noise Figure vs. Frequency



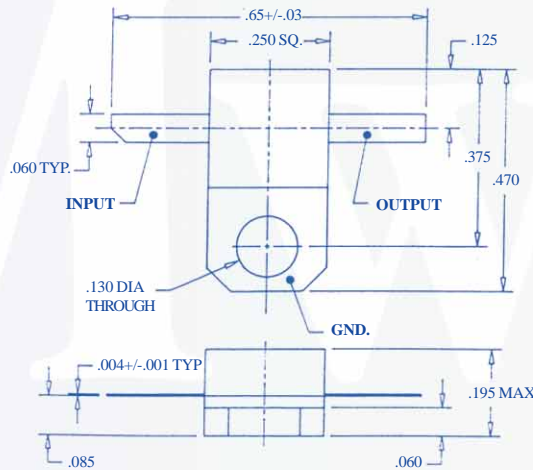
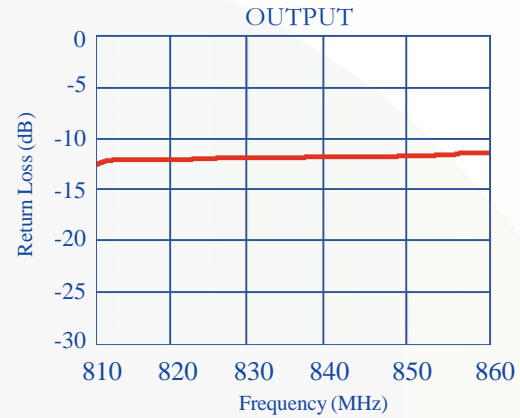
## Absolute Maximum Ratings

Maximum Bias Voltage	7.0 V
Maximum Continuous RF Input Power	240 mW
Maximum Peak Input Power	360 mW
Maximum Case Operating Temperature	+85°C
Maximum Storage Temperature	-65°C to +150°C

### Return Loss vs. Frequency



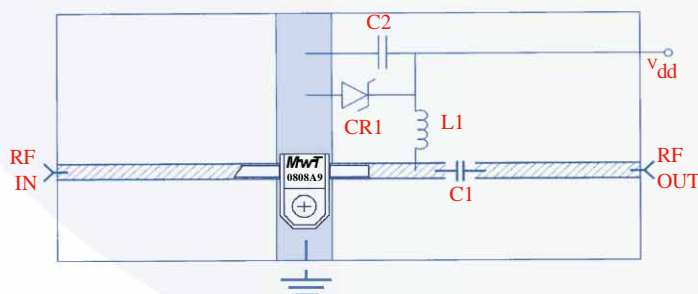
### Return Loss vs. Frequency



Pin	Connection
1	N/C
2	N/C
3	RF Input
4	N/C
5	N/C
6	N/C
7	N/C
8	RF Output, Vdd
9	N/C
10	N/C
Case	Ground

### Outline Diagrams

### Application Circuit



C1	100 pF	Chip Capacitor
C2	.22 $\mu$ F	Capacitor
L1	160 nH	Printer or Wound Coil
CR1	8.0 V	Zener Diode
		50 $\Omega$ Microstrip Line